

DMN4035LQ-7 Datasheet



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DiGi Electronics Part Number	DMN4035LQ-7-DG
Manufacturer	Diodes Incorporated
Manufacturer Product Number	DMN4035LQ-7
Description	MOSFET N-CH 40V 4.6A SOT23
Detailed Description	N-Channel 40 V 4.6A (Ta) 720mW Surface Mount SO T-23-3



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Purchase and inquiry

Manufacturer Product Number:

DMN4035LQ-7

Series:

-

FET Type:

N-Channel

Drain to Source Voltage (Vdss):

40 V

Drive Voltage (Max Rds On, Min Rds On):

4.5V, 10V

Vgs(th) (Max) @ Id:

3V @ 250µA

Vgs (Max):

±20V

FET Feature:

-

Operating Temperature:

-55°C ~ 150°C (Tj)

Qualification:

AEC-Q101

Supplier Device Package:

SOT-23-3

Base Product Number:

DMN4035

Manufacturer:

Diodes Incorporated

Product Status:

Active

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

4.6A (Ta)

Rds On (Max) @ Id, Vgs:

42mOhm @ 4.3A, 10V

Gate Charge (Qg) (Max) @ Vgs:

12.5 nC @ 10 V

Input Capacitance (Ciss) (Max) @ Vds:

574 pF @ 20 V

Power Dissipation (Max):

720mW

Grade:

Automotive

Mounting Type:

Surface Mount

Package / Case:

TO-236-3, SC-59, SOT-23-3

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.21.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99



DMN4035LQ

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max
40V	42mΩ @ V _{GS} = 10V	4.6A
	52mΩ @ V _{GS} = 4.5V	4.1A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DIODES™ DMN4035LQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**

<https://www.diodes.com/quality/product-definitions/>

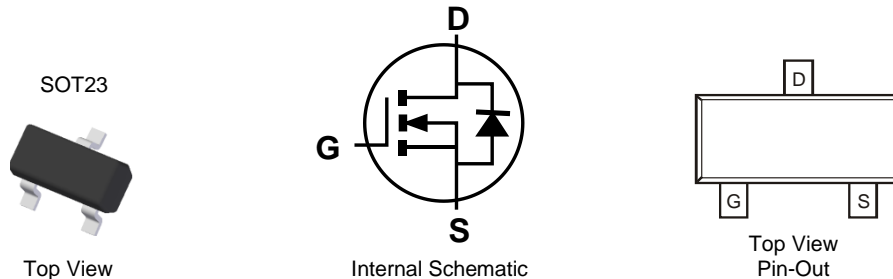
Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Battery charging
- Power management functions
- DC-DC converters
- Portable power adaptors

Mechanical Data

- Package: SOT23
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)

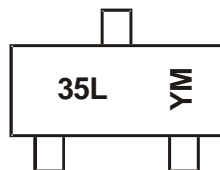


Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMN4035LQ-7	SOT23	3000	Tape & Reel
DMN4035LQ-13	SOT23	10000	Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



35L = Product Type Marking Code
 YM = Date Code Marking
 Y or Y = Year (ex: J = 2022)
 M = Month (ex: 9 = September)

Date Code Key

Year	2019	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	G	J	K	L	M	N	O	P	R	S	T
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D



DMN4035LQ

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	40	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 5) V _{GS} = 10V	Steady State	T _A = +25°C	I _D	4.6	A
		T _A = +70°C		3.7	
Maximum Body Diode Forward Current (Note 5)			I _S	4.6	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I _{DM}	25	A
Pulsed Source Current (10μs Pulse, Duty Cycle = 1%)			I _{SM}	25	A

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Power Dissipation (Note 6)		P _D	0.72	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	171	°C/W
Power Dissipation (Note 5)		P _D	1.4	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	93	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	40	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 40V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1	—	3	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	30	42	mΩ	V _{GS} = 10V, I _D = 4.3A
		—	40	52		V _{GS} = 4.5V, I _D = 3.9A
Diode Forward Voltage	V _{SD}	—	0.7	1.1	V	V _{GS} = 0V, I _S = 1.25A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	574	—	pF	V _{DS} = 20V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{oss}	—	87.8	—		
Reverse Transfer Capacitance	C _{rss}	—	38.7	—		
Gate Resistance	R _g	—	1.6	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	5.9	—	nC	V _{DS} = 20V, I _D = 3.9A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	12.5	—		
Gate-Source Charge	Q _{gs}	—	1.7	—		
Gate-Drain Charge	Q _{gd}	—	2.2	—		
Turn-On Delay Time	t _{D(ON)}	—	3.1	—	ns	V _{DD} = 20V, V _{GS} = 10V R _L = 20Ω, R _G = 6Ω
Turn-On Rise Time	t _R	—	2.6	—		
Turn-Off Delay Time	t _{D(OFF)}	—	15	—		
Turn-Off Fall Time	t _F	—	5.5	—		
Reverse Recovery Time	t _{RR}	—	6.5	—	ns	I _F = 3.9A, dI/dt = 500A/μs
Reverse Recovery Charge	Q _{RR}	—	1.2	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.



DMN4035LQ

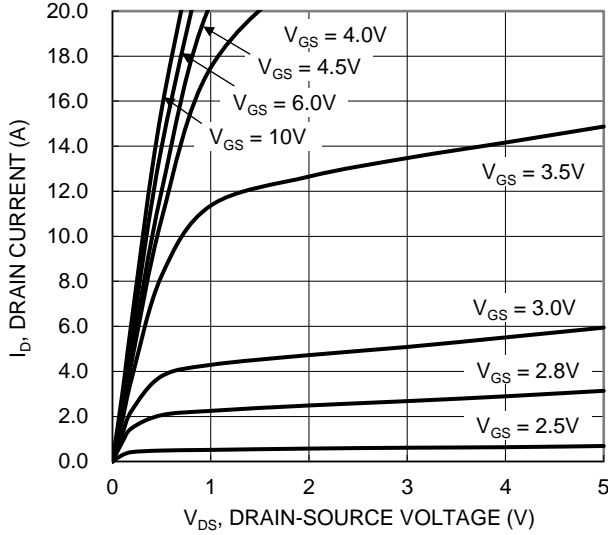


Figure 1. Typical Output Characteristic

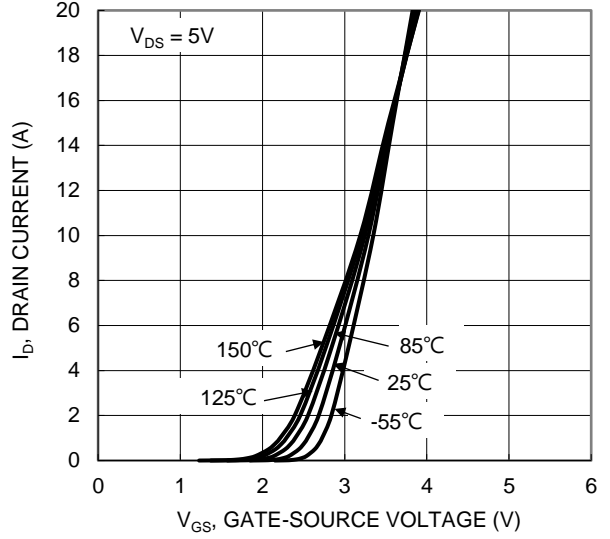


Figure 2. Typical Transfer Characteristic

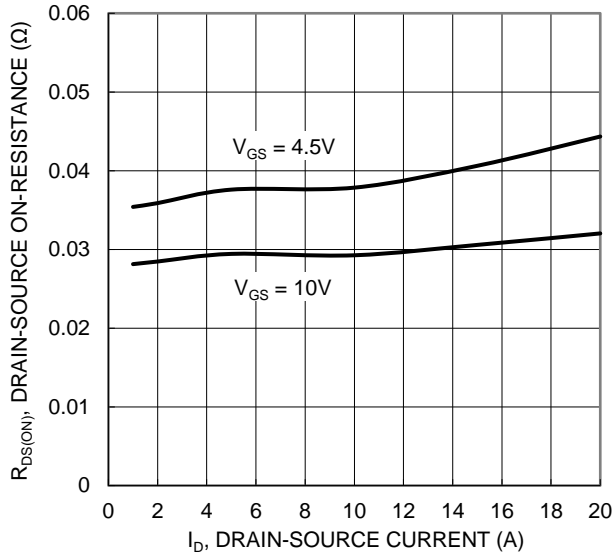


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

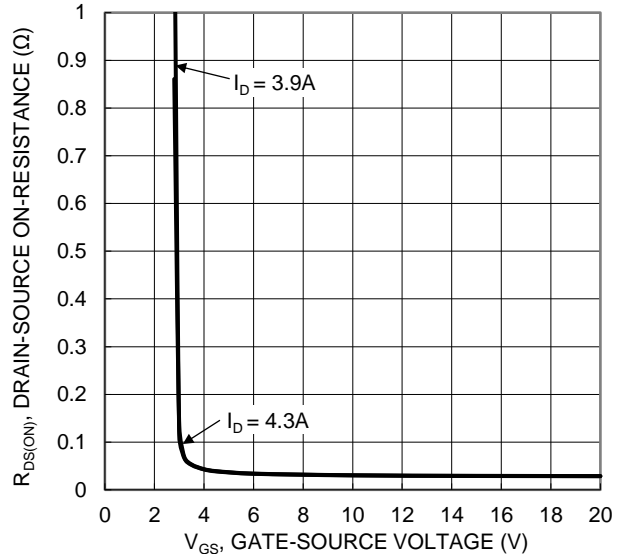


Figure 4. Typical Transfer Characteristic

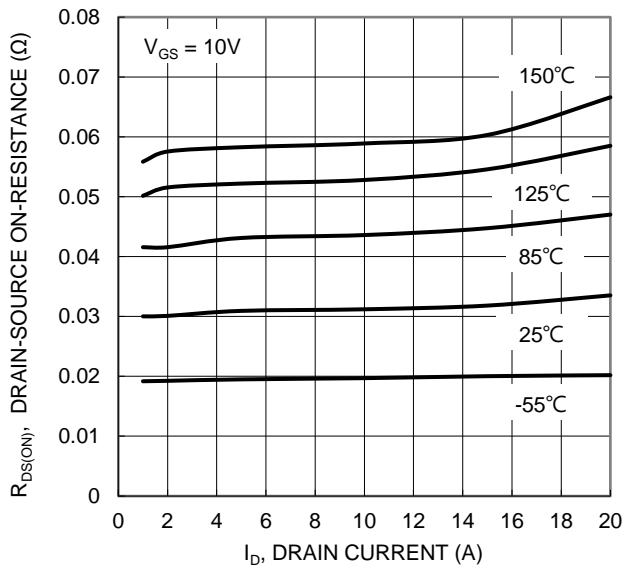


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

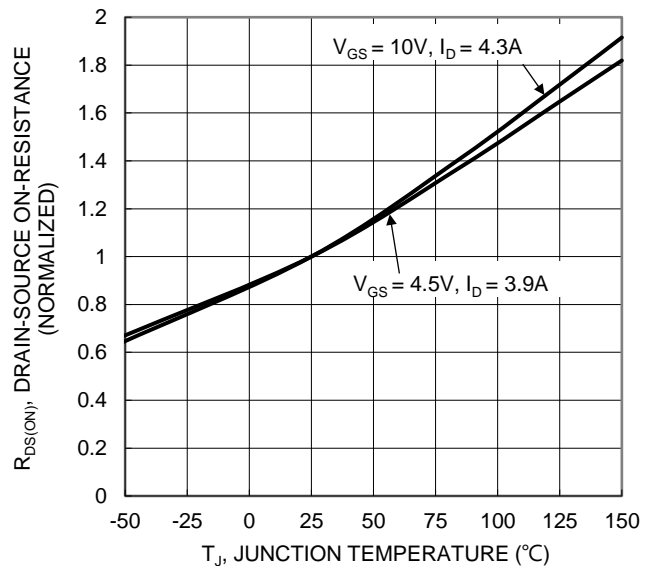


Figure 6. On-Resistance Variation with Temperature



DMN4035LQ

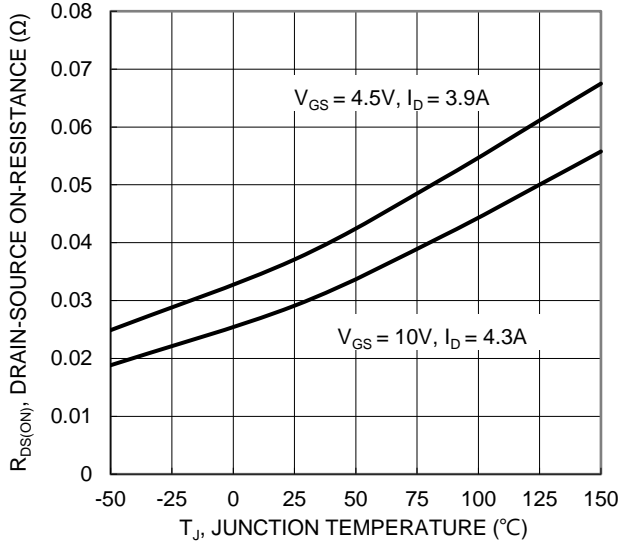


Figure 7. On-Resistance Variation with Temperature

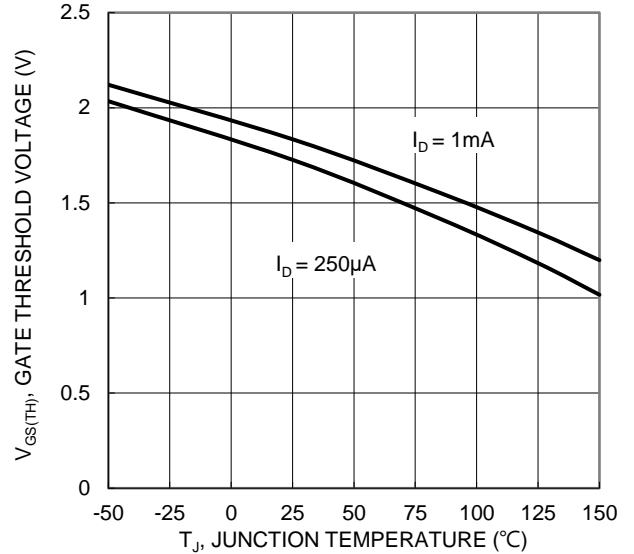


Figure 8. Gate Threshold Variation vs. Junction Temperature

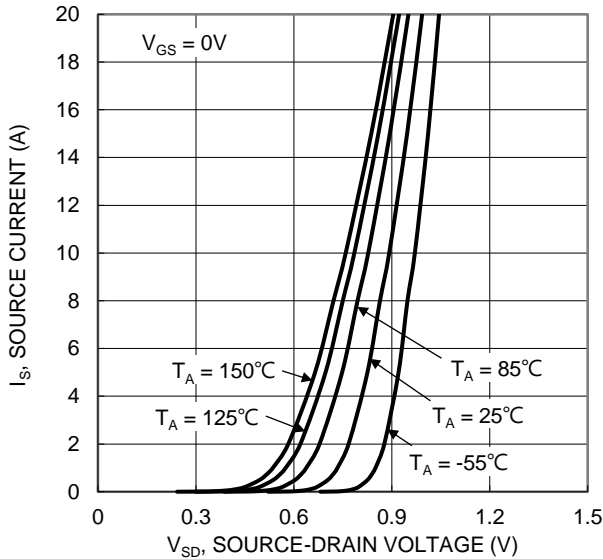


Figure 9. Diode Forward Voltage vs. Current

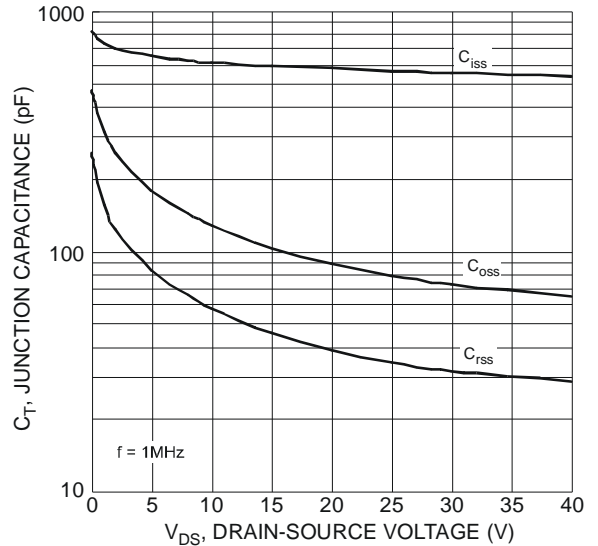


Figure 10. Typical Junction Capacitance

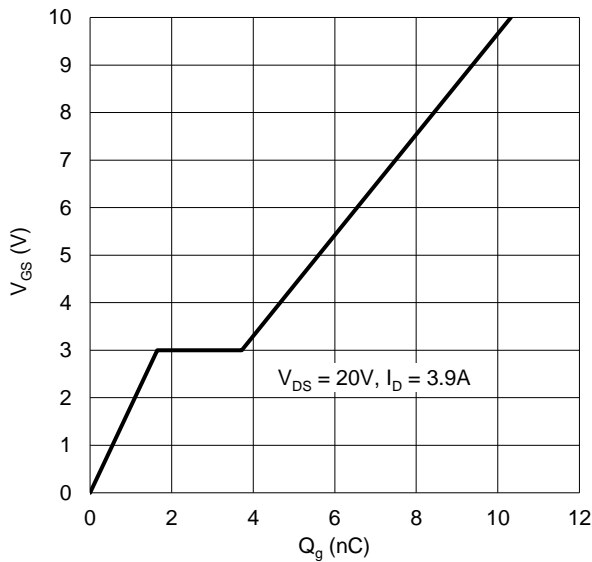


Figure 11. Gate Charge

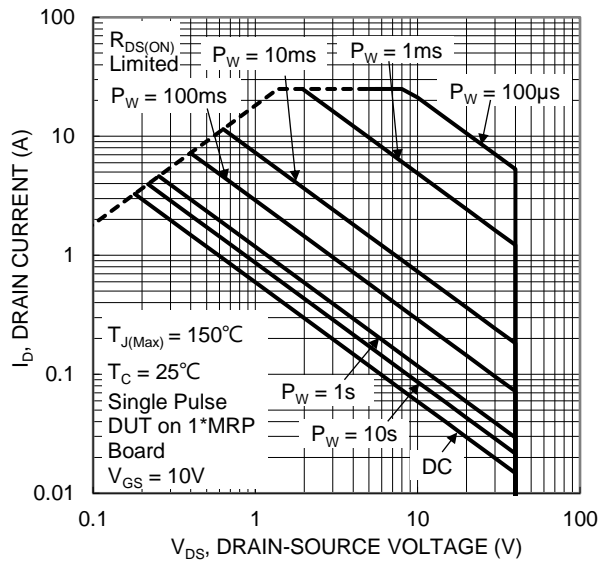


Figure 12. SOA, Safe Operation Area



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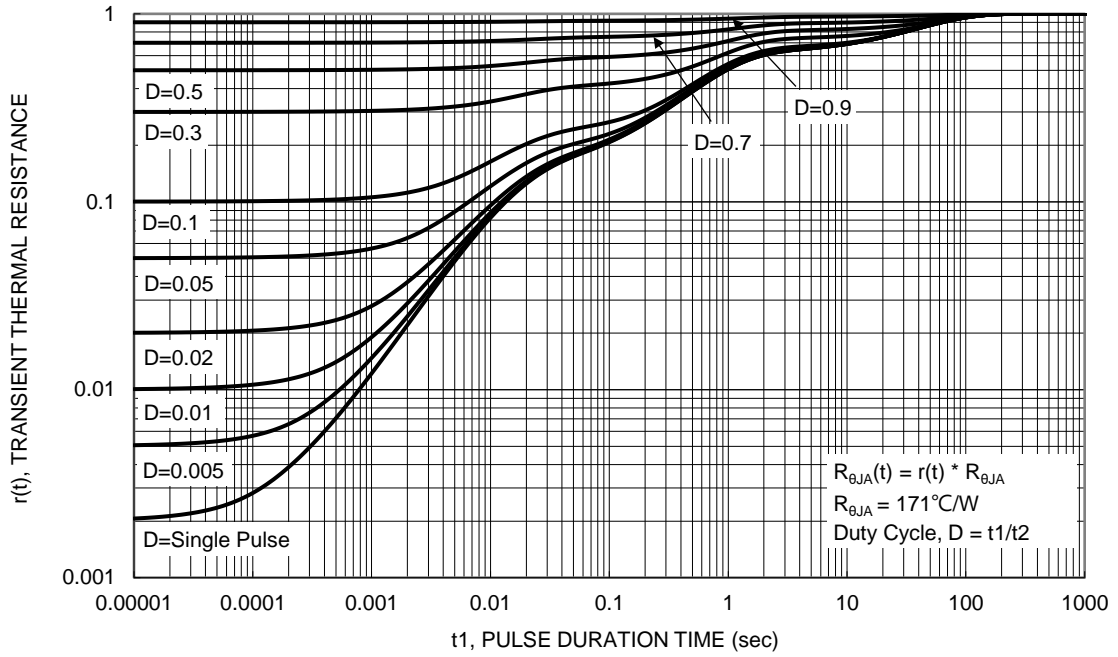
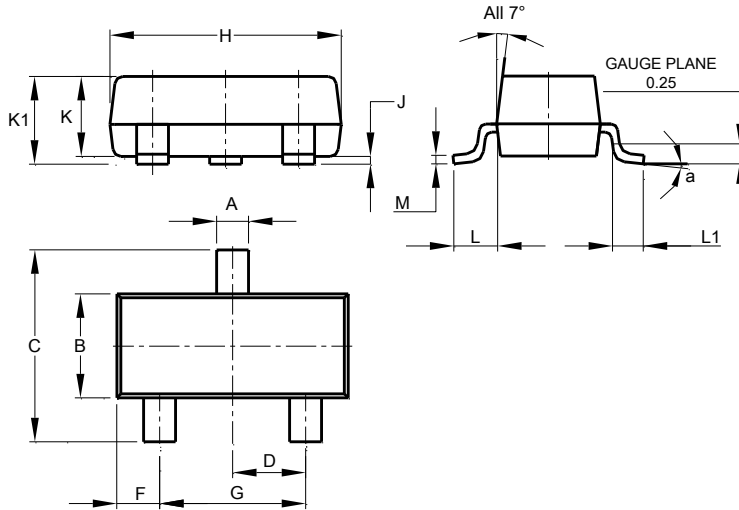


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23

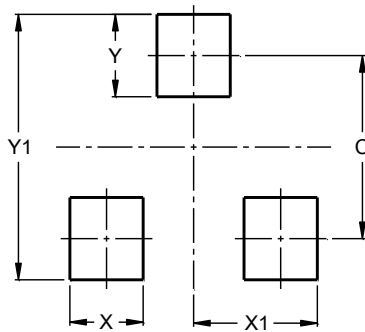


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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